

TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type
(Four High Gain Power Transistors in One)

MP4304

High Power Switching Applications

Hammer Drive, Pulse Motor Drive and Inductive Load Switching

- Small package by full molding (SIP 12 pin)
- High collector power dissipation (4-device operation)
: $P_T = 4.4 \text{ W}$ ($T_a = 25^\circ\text{C}$)
- High collector current: $I_C \text{ (DC)} = 3 \text{ A}$ (max)
- High DC current gain: $h_{FE} = 600$ (min) ($V_{CE} = 2 \text{ V}$, $I_C = 1 \text{ A}$)

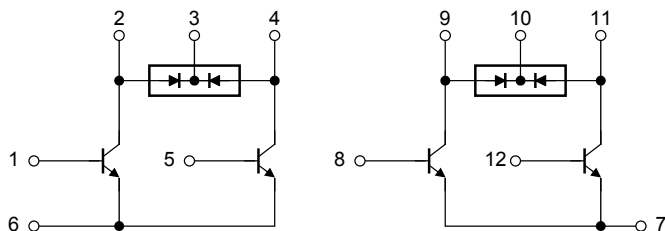
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

| Characteristics | | Symbol | Rating | Unit |
|---|-------|-----------|------------|------------------|
| Collector-base voltage | | V_{CB0} | 80 | V |
| Collector-emitter voltage | | V_{CE0} | 80 | V |
| Emitter-base voltage | | V_{EB0} | 7 | V |
| Collector current | DC | I_C | 3 | A |
| | Pulse | I_{CP} | 5 | |
| Continuous base current | | I_B | 0.5 | A |
| Collector power dissipation (1-device operation) | | P_C | 2.2 | W |
| Collector power dissipation (4-device operation) | | P_T | 4.4 | W |
| Junction temperature | | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature range | | T_{stg} | -55 to 150 | $^\circ\text{C}$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

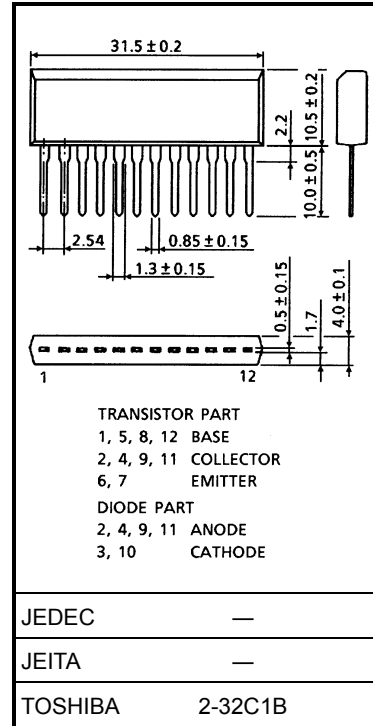
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Array Configuration



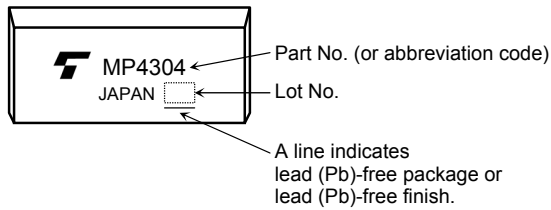
Industrial Applications

Unit: mm



Weight: 3.9 g (typ.)

Marking



Thermal Characteristics

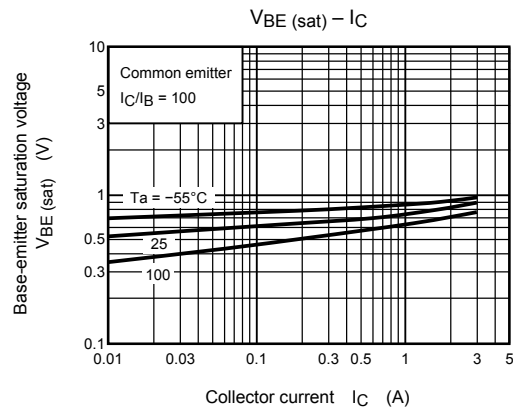
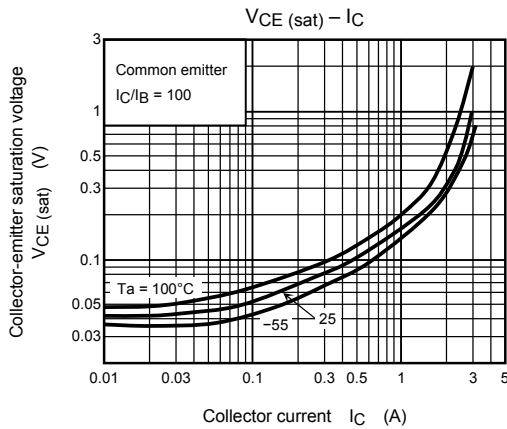
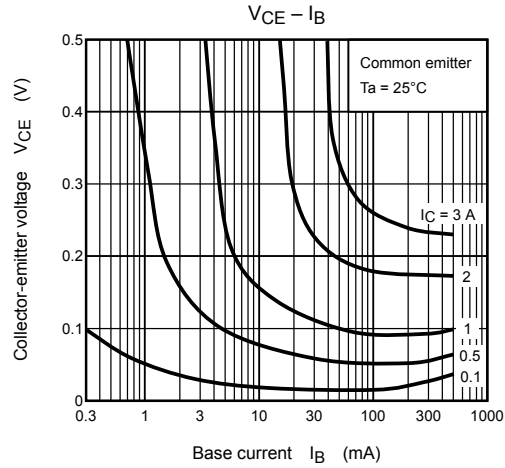
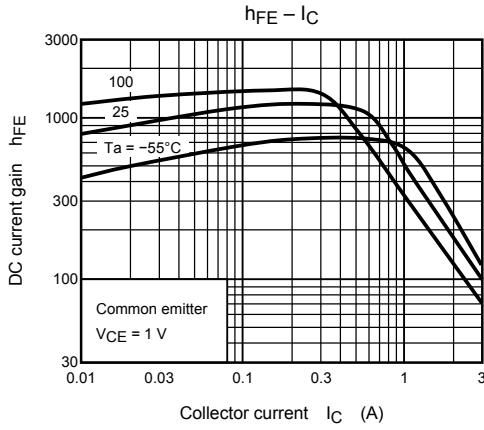
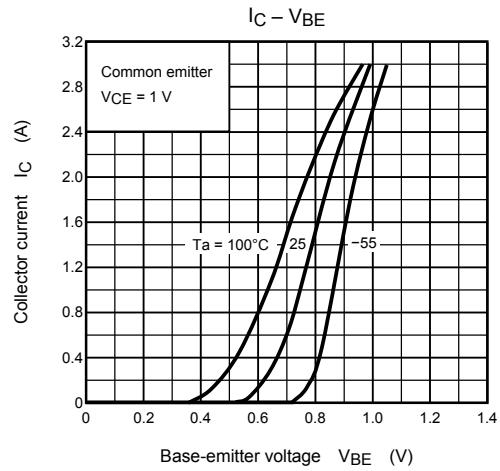
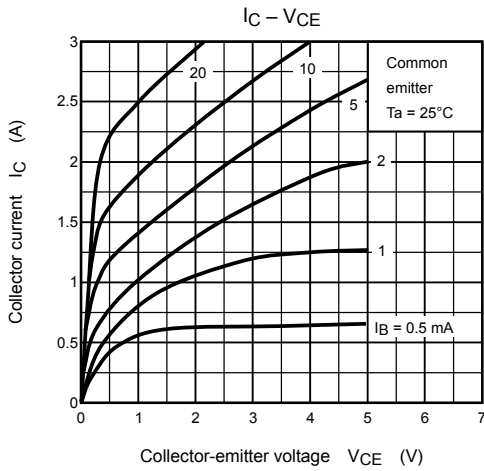
| Characteristics | Symbol | Max | Unit |
|--|----------------------|------|--------------------|
| Thermal resistance from junction to ambient (4-device operation, $T_a = 25^\circ\text{C}$) | $\Sigma R_{th(j-a)}$ | 28.4 | $^\circ\text{C/W}$ |
| Maximum lead temperature for soldering purposes (3.2 mm from case for 10 s) | T_L | 260 | $^\circ\text{C}$ |

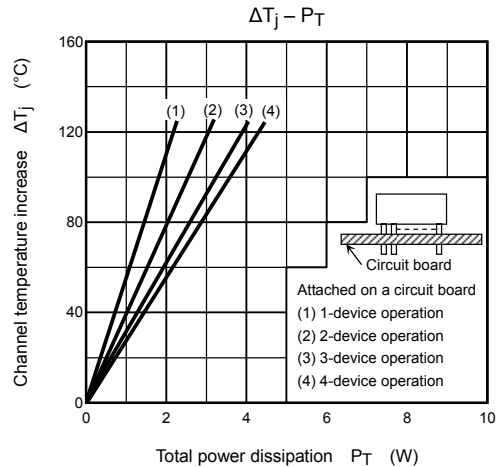
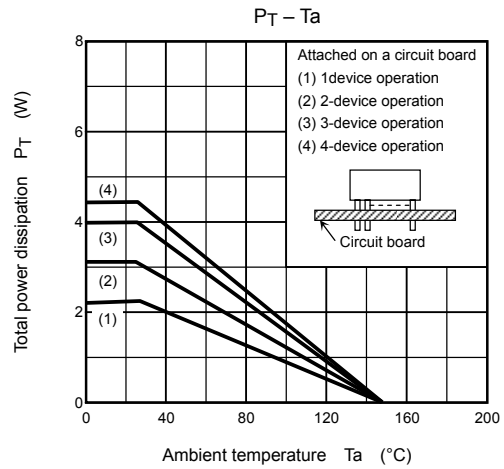
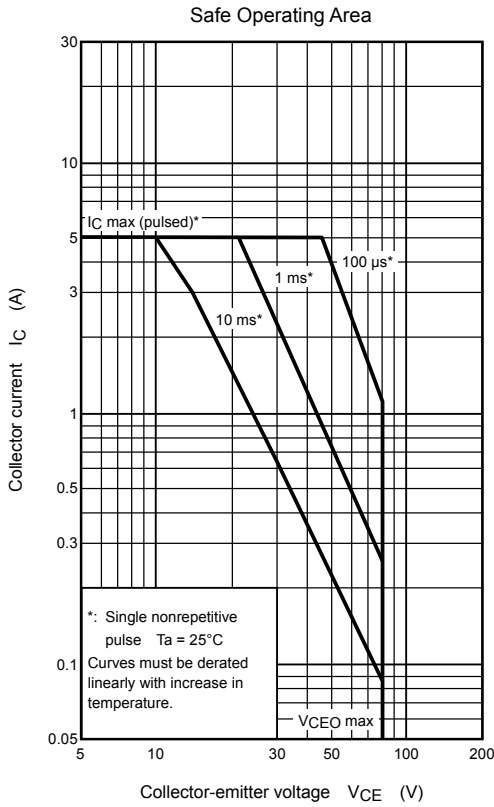
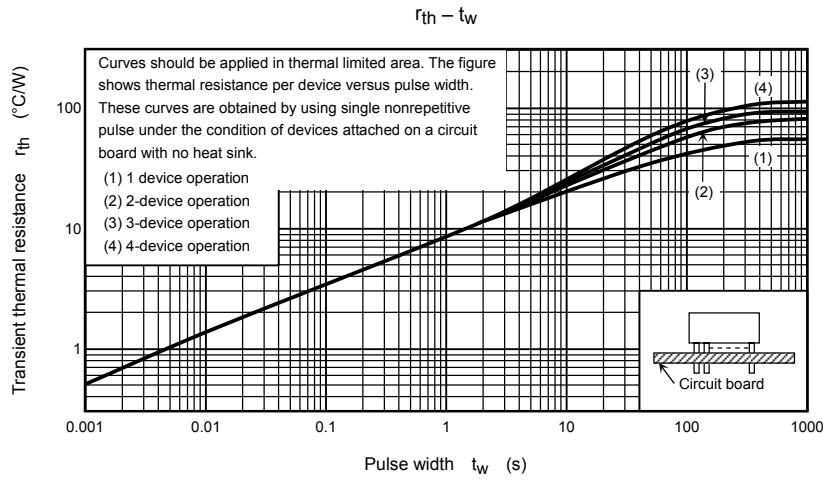
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

| Characteristics | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|-------------------------------------|-------------------|---------------|---|-----|------|-----|---------------|
| Collector cut-off current | | I_{CBO} | $V_{CB} = 80\text{ V}, I_E = 0\text{ A}$ | — | — | 10 | μA |
| Emitter cut-off current | | I_{EBO} | $V_{EB} = 7\text{ V}, I_C = 0\text{ A}$ | — | — | 10 | μA |
| Collector-base breakdown voltage | | $V_{(BR)CBO}$ | $I_C = 1\text{ mA}, I_E = 0\text{ A}$ | 80 | — | — | V |
| Collector-emitter breakdown voltage | | $V_{(BR)CEO}$ | $I_C = 10\text{ mA}, I_B = 0\text{ A}$ | 80 | — | — | V |
| DC current gain | | $h_{FE(1)}$ | $V_{CE} = 2\text{ V}, I_C = 1\text{ A}$ | 600 | — | — | — |
| | | $h_{FE(2)}$ | $V_{CE} = 2\text{ V}, I_C = 2\text{ A}$ | 150 | — | — | — |
| Saturation voltage | Collector-emitter | $V_{CE(sat)}$ | $I_C = 1.5\text{ A}, I_B = 15\text{ mA}$ | — | 0.25 | 0.5 | V |
| | Base-emitter | $V_{BE(sat)}$ | $I_C = 1.5\text{ A}, I_B = 15\text{ mA}$ | — | — | 1.2 | |
| Transition frequency | | f_T | $V_{CE} = 2\text{ V}, I_C = 0.1\text{ A}$ | — | 85 | — | MHz |
| Collector output capacitance | | C_{ob} | $V_{CB} = 10\text{ V}, I_E = 0\text{ A}, f = 1\text{ MHz}$ | — | 50 | — | pF |
| Switching time | Turn-on time | t_{on} | <p>$I_{B1} = -I_{B2} = 15\text{ mA}, \text{duty cycle} \leq 1\%$</p> | — | 0.4 | — | μs |
| | Storage time | t_{stg} | | — | 2.6 | — | |
| | Fall time | t_f | | — | 1.3 | — | |

Flyback-Diode Rating and Characteristics ($T_a = 25^\circ\text{C}$)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|-------------------------|----------|--------------------------------|-----|------|-----|---------------|
| Maximum forward current | I_{FM} | — | — | — | 3 | A |
| Reverse current | I_R | $V_R = 80\text{ V}$ | — | — | 0.4 | μA |
| Reverse voltage | V_R | $I_R = 100\text{ }\mu\text{A}$ | 80 | — | — | V |
| Forward voltage | V_F | $I_F = 1\text{ A}$ | — | — | 1.5 | V |





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20070701-EN

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